

AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

Listing Of Claims:

1. (Currently Amended) An IC card apparatus comprising:
at least one gate electrode~~electrode~~,
a gate insulating film,
at least one source electrode~~electrode~~,
at least one drain electrode~~electrode~~, and
a semiconductor layer,
on a substrate, and
wherein said semiconductor layer is located so as to contact a patterned
~~insulating layer is located between~~ said gate insulating film only at regions which act as
channel regions of the IC card apparatus ~~and said semiconductor layer, except for a~~
channel region.

2. (New) An IC card apparatus as claimed in claim 1, wherein said semiconductor layer is an organic semiconductor layer.

3. (New) An IC card apparatus as claimed in claim 1, wherein a patterned insulating layer is located between the gate insulating film and the semiconductor layer at positions other than at said channel regions, and wherein said patterned insulating

layer is a photosensitive insulating film.

4. (New) An IC card apparatus as claimed in claim 1, wherein said substrate is a plastic substrate.

5. (New) An IC card apparatus as claimed in claim 4, wherein said plastic substrate is made of polymer material.

6. (New) An IC card apparatus as claimed in claim 1, wherein each channel region has a size which is a same size as a gate electrode, of the at least one gate electrode.

7. (New) An IC card apparatus as claimed in claim 1, wherein a patterned insulating layer is located between the gate insulating film and the semiconductor layer at positions other than at said channel regions, and wherein material of the gate insulating film is different from material of the patterned insulating layer.

8. An IC card apparatus as claimed in claim 1, wherein the channel regions, in plan view, are between respective source and drain electrodes, of the at least one source electrode and the at least one drain electrode, wherein the respective source and drain electrodes contact opposite ends of the semiconductor layer contacting the gate insulating film, and wherein the at least one gate electrode is above or beneath the semiconductor layer contacting the gate insulating film.

9. (New) An IC card apparatus as claimed in claim 8, wherein each channel region has a size which is a same size as a gate electrode, of the at least one gate electrode.

10. (New) An IC card apparatus as claimed in claim 8, wherein said semiconductor layer is an organic semiconductor layer.